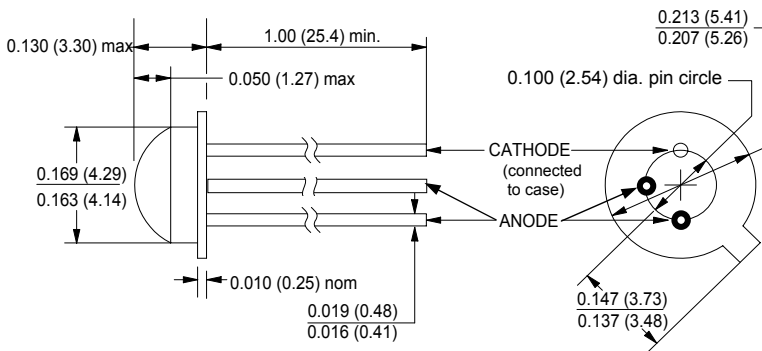


CLE334E

Very High Output Aluminum Gallium Arsenide Quad Chip IRED Array



August, 2003



Anode leads must be externally connected together.
ALL DIMENSIONS ARE IN INCHES (MILLIMETERS)

features

- 850nm wavelength
- TO-46 with epoxy-dome lens
- very wide emission angle
- > 10MHz operation
- cathode connected to case

description

The CLE334E is an advanced, high efficiency, high speed, AlGaAs infrared-emitting diode with four times the emitting surface of the typical AlGaAs emitter. High power output is achieved with four equally spaced anode contacts for higher current distribution. Anodes contacts are bonded in pairs, each pair bonded to a separate lead. Chip size is 0.030" by 0.030". The TO-46 header provides the thermal environment for reliable operation over a wide temperature range.

absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise stated)

storage temperature	-40°C to $+125^\circ\text{C}$
operating temperature	-40°C to $+100^\circ\text{C}$
lead soldering temperature ⁽¹⁾	260°C
continuous forward current ⁽²⁾⁽⁴⁾	500mA
peak forward current (1.0ms pulse width, 10% duty cycle)	4A
reverse voltage	5V
continuous power dissipation ⁽³⁾	500mW

notes:

1. 0.06" (1.5mm) from the header for 5 seconds maximum
2. Derate linearly 5.33mA/ $^\circ\text{C}$ from 25°C free air temperature to $T_A = +100^\circ\text{C}$.
3. Derate linearly 5.33mW/ $^\circ\text{C}$ from 25°C free air temperature to $T_A = +100^\circ\text{C}$.
4. Operation at this level requires a proper heat sink..

electrical characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

symbol	parameter	min	typ	max	units	test conditions
P_O	Power output ⁽⁶⁾	-	25	-	mW	$I_F = 100\text{mA}$
V_F	Forward voltage	-	1.0	1.9	V	$I_F = 100\text{mA}$
I_R	Reverse current	-	-	10	μA	$V_R = 5\text{V}$
λ_P	Peak emission wavelength	-	850	-	nm	$I_F = 100\text{mA}$
BW	Spectral bandwidth at half power points	-	35	-	nm	$I_F = 100\text{mA}$
Θ_{HP}	Emission angle at half power points	-	100	-	deg.	$I_F = 100\text{mA}$
t_r	Radiation rise time	-	20	-	ns	$I_{F(PK)} = 100\text{mA}$, $f = 1\text{kHz}$, D.C. = 50%
t_f	Radiation fall time	-	40	-	ns	$I_{F(PK)} = 100\text{mA}$, $f = 1\text{kHz}$, D.C. = 50%

Clairex reserves the right to make changes at any time to improve design and to provide the best possible product.

Revised 3/15/06